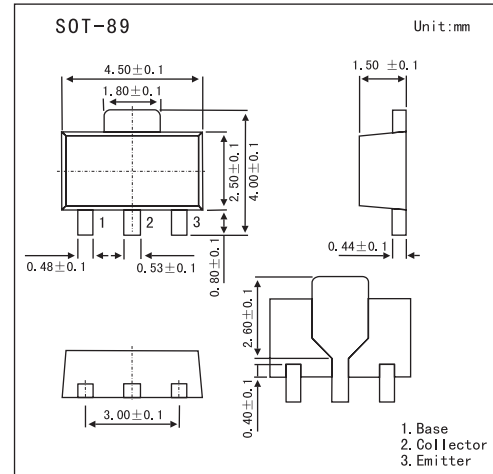


Silicon PNP Epitaxial Planar Type

2SB767

■ Features

- Large collector power dissipation PC
- High collector-emitter voltage (Base open) V_{CEO}
- Mini type package, allowing downsizing of the equipment and automatic



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-80	V
Collector-emitter voltage	V _{CEO}	-80	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-1	A
Peak collector current	I _{CP}	-0.5	A
Collector power dissipation	P _C	1	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base cutoff current	I _{CB0}	V _{CB} = -20 V, I _E = 0			-0.1	μA
Collector-base voltage	V _{CB0}	I _C = -10μA, I _E = 0	-80			V
Collector-emitter voltage	V _{CEO}	I _C = -100μA, I _B = 0	-80			V
Emitter-base voltage	V _{EB0}	I _E = -10 μA, I _C = 0	-5			V
Forward current transfer ratio	h _{FE}	V _{CE} = -10 V, I _C = -150 mA	90		220	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -300 mA, I _B = -30 mA		-0.2	-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -300 mA, I _B = -30 mA		0.85	-1.2	V
Transition frequency	f _T	V _{CB} = -10 V, I _E = 50 mA, f = 200 MHz		120		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz		20	30	pF

■ h_{FE} Classification

Marking	CQ	CR
h _{FE}	90~155	130~220